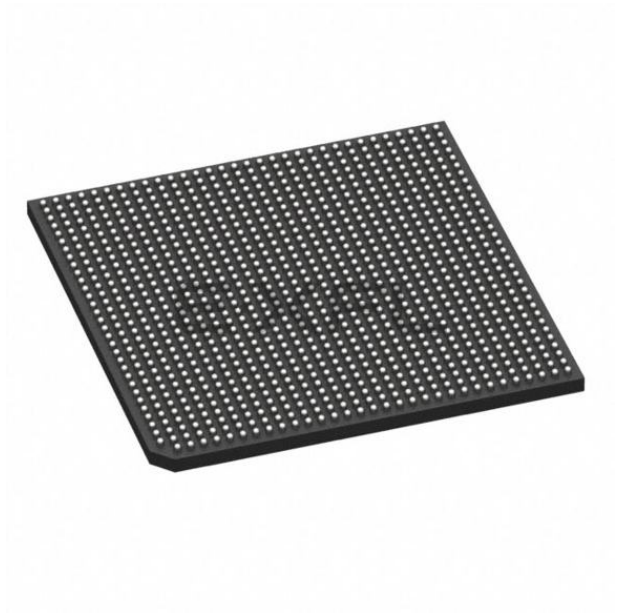

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e600
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	1.333GHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	1023-BCBGA, FCCBGA
Supplier Device Package	1023-FCCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc8641dtvu1333jc

Table 2. Recommended Operating Conditions (continued)

Characteristic		Symbol	Recommended Value	Unit	Notes
SerDes Serial I/O Supply Port 1		XV_{DD}_SRDS1	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
SerDes Serial I/O Supply Port 2		XV_{DD}_SRDS2	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
SerDes DLL and PLL supply voltage for Port 1 and Port 2		AV_{DD}_SRDS1, AV_{DD}_SRDS2	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
Platform Supply voltage		V_{DD}_PLAT	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
Local Bus and Platform PLL supply voltage		AV_{DD}_LB, AV_{DD}_PLAT	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
DDR and DDR2 SDRAM I/O supply voltages		D1_GV_{DD}, D2_GV_{DD}	2.5 V ± 125 mV	V	9
			1.8 V ± 90 mV	V	9
eTSEC 1 and 2 I/O supply voltage		LV_{DD}	3.3 V ± 165 mV	V	10
			2.5 V ± 125 mV	V	10
eTSEC 3 and 4 I/O supply voltage		TV_{DD}	3.3 V ± 165 mV	V	10
			2.5 V ± 125 mV	V	10
Local Bus, DUART, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, I^2C, JTAG and Miscellaneous I/O voltage		OV_{DD}	3.3 V ± 165 mV	V	5
Input voltage	DDR and DDR2 SDRAM signals	D*n*_MV_{IN}	GND to D*n*_GV_{DD}	V	3, 6
	DDR and DDR2 SDRAM reference	D*n*_MV_{REF}	D*n*_GV_{DD}/2 ± 1%	V	
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to LV_{DD} GND to TV_{DD}	V	4, 6
	DUART, Local Bus, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, I^2C, JTAG and Miscellaneous I/O voltage	OV_{IN}	GND to OV_{DD}	V	5,6

Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value	Unit	Notes
Junction temperature range	T_J	0 to 105	°C	—

Notes:

1. Core 1 characteristics apply only to MPC8641D
2. If two separate power supplies are used for V_{DD}_Core0 and V_{DD}_Core1, they must be at the same nominal voltage and the individual power supplies must be tracked and kept within 100 mV of each other during normal run time.
3. **Caution:** D*n*_MV_{IN} must meet the overshoot/undershoot requirements for D*n*_GV_{DD} as shown in Figure 2.
4. **Caution:** L/TV_{IN} must meet the overshoot/undershoot requirements for L/TV_{DD} as shown in Figure 2 during regular run time.
5. **Caution:** OV_{IN} must meet the overshoot/undershoot requirements for OV_{DD} as shown in Figure 2 during regular run time.
6. Timing limitations for M,L,T,O)V_{IN} and D*n*_MV_{REF} during regular run time is provided in Figure 2
7. Applies to devices marked with a core frequency of 1333 MHz and below. Refer to Table 74 Part Numbering Nomenclature to determine if the device has been marked for a core frequency of 1333 MHz and below.
8. Applies to devices marked with a core frequency above 1333 MHz. Refer to Table 74 Part Numbering Nomenclature to determine if the device has been marked for a core frequency above 1333 MHz.
9. The 2.5 V ± 125 mV range is for DDR and 1.8 V ± 90 mV range is for DDR2.
10. See Section 8.2, "FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications," for details on the recommended operating conditions per protocol.
11. The PCI Express interface of the device is expected to receive signals from 0.175 to 1.2 V. For more information refer to Section 14.4.3, "Differential Receiver (RX) Input Specifications."
12. Applies to Part Number MC8641xxx1000NX only. V_{DD}_Core*n* = 0.95 V and V_{DD}_PLAT = 1.05 V devices. Refer to Table 74 Part Numbering Nomenclature to determine if the device has been marked for V_{DD}_Core*n* = 0.95 V.
13. This voltage is the input to the filter discussed in Section 20.2, "Power Supply Design and Sequencing," and not necessarily the voltage at the AV_{DD}_Core*n* pin, which may be reduced from V_{DD}_Core*n* by the filter.

Table 15 provides the recommended operating conditions for the DDR SDRAM component(s) when D*n*_GV_{DD}(typ) = 2.5 V.

Table 15. DDR SDRAM DC Electrical Characteristics for D*n*_GV_{DD} (typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	D*n*_GV_{DD}	2.375	2.625	V	1
I/O reference voltage	D*n*_MV_{REF}	0.49 × D*n*_GV_{DD}	0.51 × D*n*_GV_{DD}	V	2
I/O termination voltage	V_{TT}	D*n*_MV_{REF} – 0.04	D*n*_MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	D*n*_MV_{REF} + 0.15	D*n*_GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	D*n*_MV_{REF}– 0.15	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. D*n*_GV_{DD} is expected to be within 50 mV of the DRAM D*n*_GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × D*n*_GV_{DD}, and to track D*n*_GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on D*n*_MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to D*n*_MV_{REF}. This rail should track variations in the DC level of D*n*_MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ D*n*_GV_{DD}.

Table 16 provides the DDR capacitance when D*n*_GV_{DD} (typ)=2.5 V.

Table 16. DDR SDRAM Capacitance for D*n*_GV_{DD} (typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. D*n*_GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = D*n*_GVDD/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 17 provides the current draw characteristics for MV_{REF}.

Table 17. Current Draw Characteristics for MV_{REF}

Parameter / Condition	Symbol	Min	Max	Unit	Note
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 18 provides the input AC timing specifications for the DDR2 SDRAM when D*n*_GV_{DD}(typ)=1.8 V.

Table 18. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage 400, 533 MHz 600 MHz	V_{IL}	—	 D*n*_MV_{REF} – 0.25 D*n*_MV_{REF} – 0.20	V	—
AC input high voltage 400, 533 MHz 600 MHz	V_{IH}	 D*n*_MV_{REF} + 0.25 D*n*_MV_{REF} + 0.20	—	V	—

Table 19 provides the input AC timing specifications for the DDR SDRAM when D*n*_GV_{DD}(typ)=2.5 V.

Table 19. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	D*n*_MV_{REF} – 0.31	V	—
AC input high voltage	V_{IH}	D*n*_MV_{REF} + 0.31	—	V	—

Table 20 provides the input AC timing specifications for the DDR SDRAM interface.

Table 20. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC	t_{CISKEW}	—		ps	1, 2
600 MHz	—	–240	240	—	3
533 MHz	—	–300	300	—	3
400 MHz	—	–365	365	—	—

Note:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}.This can be determined by the following equation: t_{DISKEW} =+/–(T/4 – abs(t_{CISKEW})) where T is the clock period and abs(t_{CISKEW}) is the absolute value of t_{CISKEW}.
3. Maximum DDR1 frequency is 400 MHz.

clock to synchronously generate transmit data and outputs an echoed copy of the transmit clock back out onto the TSEC*n*_GTX_CLK pin (while transmit data appears on TSEC*n*_TXD[7:0], for example). It is intended that external receivers capture eTSEC transmit data using the clock on TSEC*n*_GTX_CLK as a source-synchronous timing reference. Typically, the clock edge that launched the data can be used, since the clock is delayed by the eTSEC to allow acceptable set-up margin at the receiver. Note that there is relationship between the maximum FIFO speed and the platform speed. For more information see Section 18.4.2, "Platform to FIFO Restrictions."

NOTE

The phase between the output clocks TSEC1_GTX_CLK and TSEC2_GTX_CLK (ports 1 and 2) is no more than 100 ps. The phase between the output clocks TSEC3_GTX_CLK and TSEC4_GTX_CLK (ports 3 and 4) is no more than 100 ps.

A summary of the FIFO AC specifications appears in Table 26 and Table 27.

Table 26. FIFO Mode Transmit AC Timing Specification

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5% and 2.5 V ± 5%.

Parameter/Condition	Symbol	Min	Typ	Max	Unit
TX_CLK, GTX_CLK clock period (GMII mode)	t_{FIT}	7.0	8.0	100	ns
TX_CLK, GTX_CLK clock period (Encoded mode)	t_{FIT}	5.3	8.0	100	ns
TX_CLK, GTX_CLK duty cycle	t_{FITH}/t_{FIT}	45	50	55	%
TX_CLK, GTX_CLK peak-to-peak jitter	t_{FITJ}	—	—	250	ps
Rise time TX_CLK (20%–80%)	t_{FITR}	—	—	0.75	ns
Fall time TX_CLK (80%–20%)	t_{FITF}	—	—	0.75	ns
FIFO data TXD[7:0], TX_ER, TX_EN setup time to GTX_CLK	t_{FITDV}	2.0	—	—	ns
GTX_CLK to FIFO data TXD[7:0], TX_ER, TX_EN hold time	t_{FITDX}	0.5	—	3.0	ns

Table 27. FIFO Mode Receive AC Timing Specification

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5% and 2.5 V ± 5%.

Parameter/Condition	Symbol	Min	Typ	Max	Unit
RX_CLK clock period (GMII mode)	t_{FIR}[1]	7.0	8.0	100	ns
RX_CLK clock period (Encoded mode)	t_{FIR}[1]	5.3	8.0	100	ns
RX_CLK duty cycle	t_{FIRH}/t_{FIR}	45	50	55	%
RX_CLK peak-to-peak jitter	t_{FIRJ}	—	—	250	ps
Rise time RX_CLK (20%–80%)	t_{FIRR}	—	—	0.75	ns
Fall time RX_CLK (80%–20%)	t_{FIRF}	—	—	0.75	ns
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{FIRDV}	1.5	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{FIRDX}	0.5	—	—	ns

[1] ±100 ppm tolerance on RX_CLK frequency

8.2.3 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.3.1 MII Transmit AC Timing Specifications

Table 30 provides the MII transmit AC timing specifications.

Table 30. MII Transmit AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}[2]	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise time (20%-80%)	t_{MTXR}[2]	1.0	—	4.0	ns
TX_CLK data clock fall time (80%-20%)	t_{MTXF}[2]	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

Figure 13 shows the MII transmit AC timing diagram.

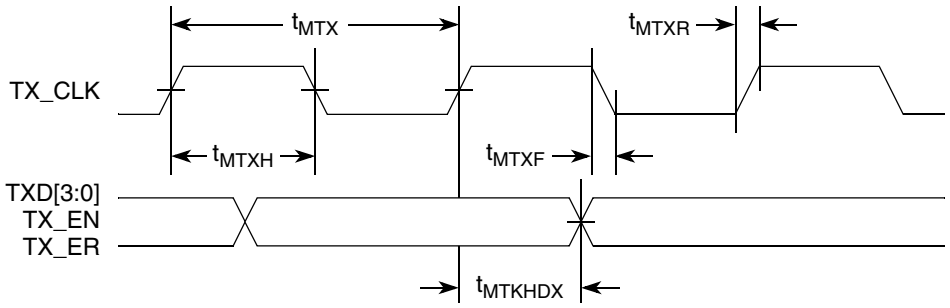


Figure 13. MII Transmit AC Timing Diagram

13.2.3 Interfacing With Other Differential Signaling Levels

With on-chip termination to SGND, the differential reference clocks inputs are HCSL (High-Speed Current Steering Logic) compatible DC-coupled.

Many other low voltage differential type outputs like LVDS (Low Voltage Differential Signaling) can be used but may need to be AC-coupled due to the limited common mode input range allowed (100 to 400 mV) for DC-coupled connection.

LVPECL outputs can produce signal with too large amplitude and may need to be DC-biased at clock driver output first, then followed with series attenuation resistor to reduce the amplitude, in addition to AC-coupling.

NOTE

Figure 43 to Figure 46 below are for conceptual reference only. Due to the fact that clock driver chip's internal structure, output impedance and termination requirements are different between various clock driver chip manufacturers, it is very possible that the clock circuit reference designs provided by clock driver chip vendor are different from what is shown below. They might also vary from one vendor to the other. Therefore, Freescale Semiconductor can neither provide the optimal clock driver reference circuits, nor guarantee the correctness of the following clock driver connection reference circuits. The system designer is recommended to contact the selected clock driver chip vendor for the optimal reference circuits with the MPC8641D SerDes reference clock receiver requirement provided in this document.

Figure 43 shows the SerDes reference clock connection reference circuits for HCSL type clock driver. It assumes that the DC levels of the clock driver chip is compatible with MPC8641D SerDes reference clock input's DC requirement.

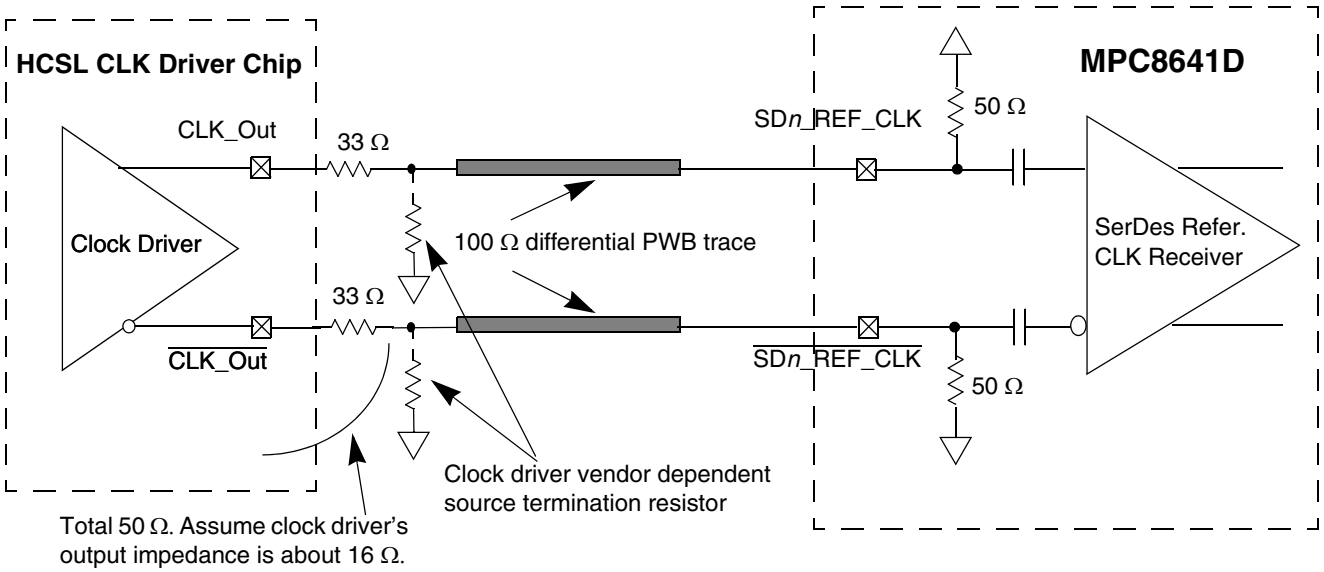


Figure 43. DC-Coupled Differential Connection with HCSL Clock Driver (Reference Only)

Figure 44 shows the SerDes reference clock connection reference circuits for LVDS type clock driver. Since LVDS clock driver's common mode voltage is higher than the MPC8641D SerDes reference clock input's allowed range (100 to 400 mV), AC-coupled connection scheme must be used. It assumes the LVDS output driver features 50-Ω termination resistor. It also assumes that the LVDS transmitter establishes its own common mode level without relying on the receiver or other external component.

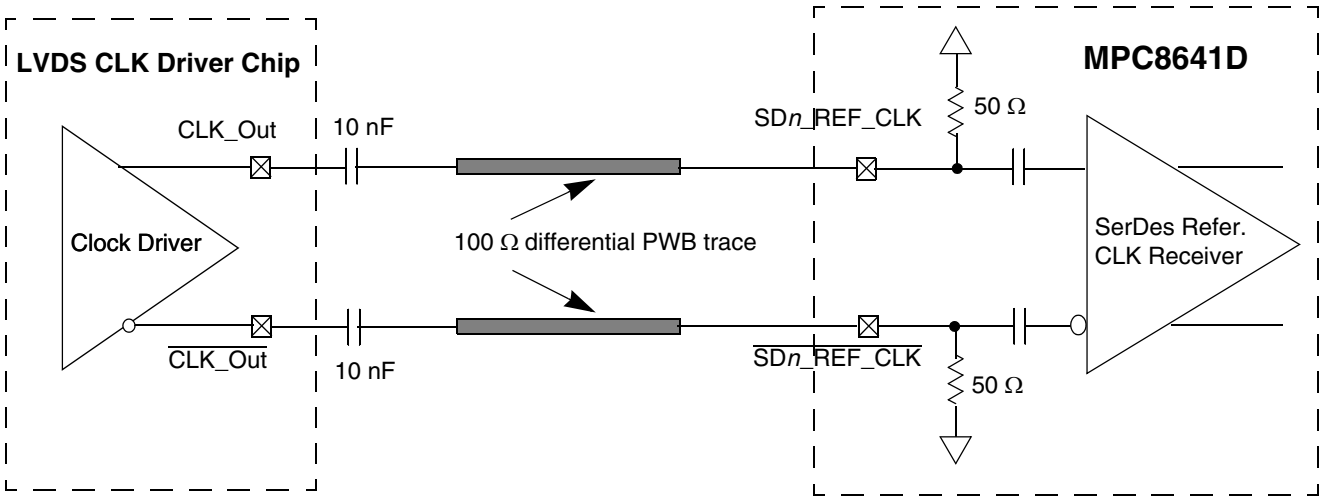


Figure 44. AC-Coupled Differential Connection with LVDS Clock Driver (Reference Only)

Figure 45 shows the SerDes reference clock connection reference circuits for LVPECL type clock driver. Since LVPECL driver's DC levels (both common mode voltages and output swing) are incompatible with

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
TSEC3_TX_EN	AH19	O	TV_{DD}	36
TSEC3_TX_ER	AH17	O	TV_{DD}	—
TSEC3_TX_CLK	AH18	I	TV_{DD}	40
TSEC3_GTX_CLK	AG19	O	TV_{DD}	41
TSEC3_CRS	AE15	I/O	TV_{DD}	37
TSEC3_COL	AF15	I	TV_{DD}	—
TSEC3_RXD[0:7]	AJ17, AE16, AH16, AH14, AJ19, AH15, AG16, AE19	I	TV_{DD}	—
TSEC3_RX_DV	AG15	I	TV_{DD}	—
TSEC3_RX_ER	AF16	I	TV_{DD}	—
TSEC3_RX_CLK	AJ18	I	TV_{DD}	40
eTSEC Port 4 Signals[5]				
TSEC4_TXD[0:3]	AC18, AC16, AD18, AD17	O	TV_{DD}	6
TSEC4_TXD[4]	AD16	O	TV_{DD}	25
TSEC4_TXD[5:7]	AB18, AB17, AB16	O	TV_{DD}	6
TSEC4_TX_EN	AF17	O	TV_{DD}	36
TSEC4_TX_ER	AF19	O	TV_{DD}	—
TSEC4_TX_CLK	AF18	I	TV_{DD}	40
TSEC4_GTX_CLK	AG17	O	TV_{DD}	41
TSEC4_CRS	AB14	I/O	TV_{DD}	37
TSEC4_COL	AC13	I	TV_{DD}	—
TSEC4_RXD[0:7]	AG14, AD13, AF13, AD14, AE14, AB15, AC14, AE17	I	TV_{DD}	—
TSEC4_RX_DV	AC15	I	TV_{DD}	—
TSEC4_RX_ER	AF14	I	TV_{DD}	—
TSEC4_RX_CLK	AG13	I	TV_{DD}	40
Local Bus Signals[5]				
LAD[0:31]	A30, E29, C29, D28, D29, H25, B29, A29, C28, L22, M22, A28, C27, H26, G26, B27, B26, A27, E27, G25, D26, E26, G24, F27, A26, A25, C25, H23, K22, D25, F25, H22	I/O	OV_{DD}	6
LDP[0:3]	A24, E24, C24, B24	I/O	OV_{DD}	6, 22
LA[27:31]	J21, K21, G22, F24, G21	O	OV_{DD}	6, 22
$\overline{\text{LCS}}$[0:4]	A22, C22, D23, E22, A23	O	OV_{DD}	7
$\overline{\text{LCS}}$[5]/$\overline{\text{DMA\_DREQ}}$[2]	B23	O	OV_{DD}	7, 9, 10

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
$SENSEV_{SS}$_Core0	P14	Core0 GND sensing pin	—	31
$SENSEV_{SS}$_Core1	V20	Core1 GND sensing pin	—	12, 31, *S3*
$SENSEV_{DD}$_PLAT	N18	V_{DD}_PLAT sensing pin	—	28
$SENSEV_{SS}$_PLAT	P18	Platform GND sensing pin	—	29
$D1\_GV_{DD}$	B11, B14, D10, D13, F9, F12, H8, H11, H14, K10, K13, L8, P8, R6, U8, V6, W10, Y8, AA6, AB10, AC8, AD12, AE10, AF8, AG12, AH10, AJ8, AJ14, AK12, AL10, AL16	SDRAM 1 I/O supply	$D1\_GV_{DD}$ 2.5 - DDR 1.8 DDR2	—
$D2\_GV_{DD}$	B2, B5, B8, D4, D7, E2, F6, G4, H2, J6, K4, L2, M6, N4, P2, T4, U2, W4, Y2, AB4, AC2, AD6, AE4, AF2, AG6, AH4, AJ2, AK6, AL4, AM2	SDRAM 2 I/O supply	$D2\_GV_{DD}$ 2.5 V - DDR 1.8 V - DDR2	—
OV_{DD}	B22, B25, B28, D17, D24, D27, F19, F22, F26, F29, G17, H21, H24, K19, K23, M21, AM30	DUART, Local Bus, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, JTAG, Power management, I^2C, JTAG and Miscellaneous I/O voltage	OV_{DD} 3.3 V	—
LV_{DD}	AC20, AD23, AH22	TSEC1 and TSEC2 I/O voltage	LV_{DD} 2.5/3.3 V	—
TV_{DD}	AC17, AG18, AK20	TSEC3 and TSEC4 I/O voltage	TV_{DD} 2.5/3.3 V	—
SV_{DD}	H31, J29, K28, K32, L30, M28, M31, N29, R30, T31, U29, V32, W30, Y31, AA29, AB32, AC30, AD31, AE29, AG30, AH31, AJ29, AK32, AL30, AM31	Transceiver Power Supply SerDes	SV_{DD} 1.05/1.1 V	—
XV_{DD}_SRDS1	K26, L24, M27, N25, P26, R24, R28, T27, U25, V26	Serial I/O Power Supply for SerDes Port 1	XV_{DD}_SRDS1 1.05/1.1 V	—

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
TSEC3_TXD[6:7]/ cfg_tsec3_prtcl[0:1]	AL20, AL19	—	LV_{DD}	—
TSEC4_TXD[0:3]/ cfg_io_ports[0:3]	AC18, AC16, AD18, AD17	—	LV_{DD}	—
TSEC4_TXD[5]/ cfg_tsec4_reduce	AB18	—	LV_{DD}	—
TSEC4_TXD[6:7]/ cfg_tsec4_prtcl[0:1]	AB17, AB16	—	LV_{DD}	—
LAD[0:31]/ cfg_gpporcr[0:31]	A30, E29, C29, D28, D29, H25, B29, A29, C28, L22, M22, A28, C27, H26, G26, B27, B26, A27, E27, G25, D26, E26, G24, F27, A26, A25, C25, H23, K22, D25, F25, H22	—	OV_{DD}	—
$\overline{\text{LWE[0]}}$/ cfg_cpu_boot	E21	—	OV_{DD}	—
$\overline{\text{LWE[1]}}$/ cfg_rio_sys_size	F21	—	OV_{DD}	—
$\overline{\text{LWE[2:3]}}$/ cfg_host_agt[0:1]	D22, E20	—	OV_{DD}	—
LDP[0:3], LA[27] / cfg_core_pll[0:4]	A24, E24, C24, B24, J21	—	OV_{DD}	22
LA[28:31]/ cfg_sys_pll[0:3]	K21, G22, F24, G21	—	OV_{DD}	22
LGPL[3], LGPL[5]/ cfg_boot_seq[0:1]	K20, J19	—	OV_{DD}	—
D1_MSRCID[0]/ cfg_mem_debug	F15	—	OV_{DD}	—
D1_MSRCID[1]/ cfg_ddr_debug	K15	—	OV_{DD}	—

- Binary value on LA[28:31] at power up

Note that there is no default for this PLL ratio; these signals must be pulled to the desired values. Also note that the DDR data rate is the determining factor in selecting the MPX bus frequency, since the MPX frequency must equal the DDR data rate.

Table 68. MPX:SYSCLK Ratio

Binary Value of LA[28:31] Signals	MPX:SYSCLK Ratio
0000	Reserved
0001	Reserved
0010	2:1
0011	3:1
0100	4:1
0101	5:1
0110	6:1
0111	Reserved
1000	8:1
1001	9:1

18.3 e600 to MPX clock PLL Ratio

Table 69 describes the clock ratio between the platform and the e600 core clock. This ratio is determined by the binary value of LDP[0:3], LA[27](cfg_core_pll[0:4] - reset config name) at power up, as shown in Table 69.

Table 69. e600 Core to MPX Clock Ratio

Binary Value of LDP[0:3], LA[27] Signals	e600 core: MPX Clock Ratio
01000	2:1
01100	2.5:1
10000	3:1
11100	3.5:1
10100	4:1
01110	4.5:1

18.4 Frequency Options

18.4.1 SYSCLK to Platform Frequency Options

Table 70 shows some SYSCLK frequencies and the expected MPX frequency values based on the MPX clock to SYSCLK ratio. Note that frequencies between 400 MHz and 500 MHz are NOT supported on the platform. See note regarding *cfg_platform_freq* in Section 17, "Signal Listings," because it is a reset configuration pin that is related to platform frequency.

Table 70. Frequency Options of SYSCLK with Respect to Platform/MPX Clock Speed

MPX to SYSCLK Ratio	SYSCLK (MHz)					
	66	83	100	111	133	167
	Platform/MPX Frequency (MHz)[1]					
2						
3					400	500
4			400		533	
5			500	555		
6	400	500	600			
8	533					
9	600					

1 SYSCLK frequency range is 66-167 MHz. Platform clock/ MPX frequency range is 400 MHz, 500-600 MHz.

18.4.2 Platform to FIFO Restrictions

Please note the following FIFO maximum speed restrictions based on platform speed.

For FIFO GMII mode:

FIFO TX/RX clock frequency <= platform clock frequency/4.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 127 MHz

For FIFO encoded mode:

FIFO TX/RX clock frequency <= platform clock frequency/3.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 167 MHz

19.2.2 Thermal Interface Materials

A thermal interface material is recommended at the package-to-heat sink interface to minimize the thermal contact resistance. Figure 61 shows the thermal performance of three thin-sheet thermal-interface materials (silicone, graphite/oil, floroether oil), a bare joint, and a joint with thermal grease as a function of contact pressure. As shown, the performance of these thermal interface materials improves with increasing contact pressure. The use of thermal grease significantly reduces the interface thermal resistance. That is, the bare joint results in a thermal resistance approximately seven times greater than the thermal grease joint.

Often, heat sinks are attached to the package by means of a spring clip to holes in the printed-circuit board (see Figure 59). Therefore, synthetic grease offers the best thermal performance, considering the low interface pressure, and is recommended due to the high power dissipation of the MPC8641. Of course, the selection of any thermal interface material depends on many factors—thermal performance requirements, manufacturability, service temperature, dielectric properties, cost, and so on.

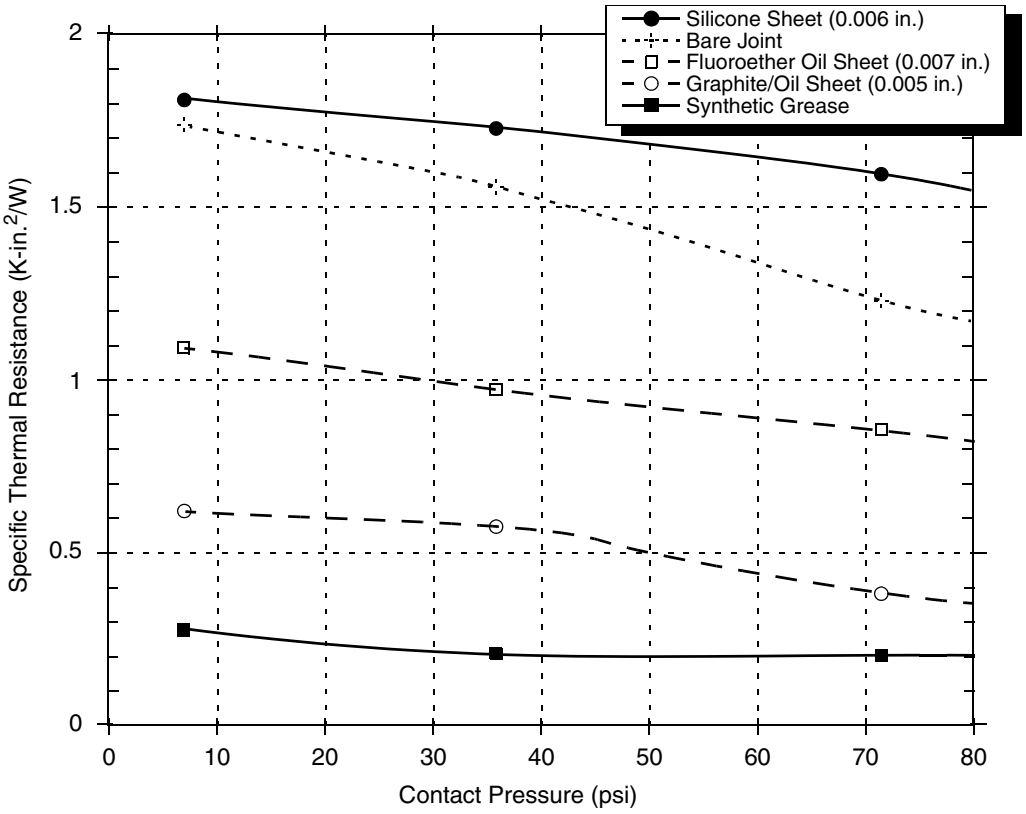


Figure 61. Thermal Performance of Select Thermal Interface Material

The board designer can choose between several types of thermal interface. Heat sink adhesive materials should be selected based on high conductivity and mechanical strength to meet equipment shock/vibration requirements. There are several commercially available thermal interfaces and adhesive materials provided by the following vendors:

example, assuming a T_i of 30°C, a T_r of 5°C, a package $R_{\theta JC}$ = 0.1, and a typical power consumption (P_d) of 43.4 W, the following expression for T_j is obtained:

Die-junction temperature: $T_j = 30°C + 5°C + (0.1°C/W + 0.2°C/W + \theta_{sa}) \times 43.4\ W$

For this example, a $R_{\theta sa}$ value of 1.32 °C/W or less is required to maintain the die junction temperature below the maximum value of Table 2.

Though the die junction-to-ambient and the heat sink-to-ambient thermal resistances are a common figure-of-merit used for comparing the thermal performance of various microelectronic packaging technologies, one should exercise caution when only using this metric in determining thermal management because no single parameter can adequately describe three-dimensional heat flow. The final die-junction operating temperature is not only a function of the component-level thermal resistance, but the system-level design and its operating conditions. In addition to the component's power consumption, a number of factors affect the final operating die-junction temperature—airflow, board population (local heat flux of adjacent components), heat sink efficiency, heat sink placement, next-level interconnect technology, system air temperature rise, altitude, and so on.

Due to the complexity and variety of system-level boundary conditions for today's microelectronic equipment, the combined effects of the heat transfer mechanisms (radiation, convection, and conduction) may vary widely. For these reasons, we recommend using conjugate heat transfer models for the board as well as system-level designs.

For system thermal modeling, the MPC8641 thermal model is shown in Figure 62. Four cuboids are used to represent this device. The die is modeled as 12.4x15.3 mm at a thickness of 0.86 mm. See Section 3, "Power Characteristics" for power dissipation details. The substrate is modeled as a single block 33x33x1.2 mm with orthotropic conductivity: 13.5 W/(m • K) in the xy-plane and 5.3 W/(m • K) in the z-direction. The die is centered on the substrate. The bump/underfill layer is modeled as a collapsed thermal resistance between the die and substrate with a conductivity of 5.3 W/(m • K) in the thickness dimension of 0.07 mm. Because the bump/underfill is modeled with zero physical dimension (collapsed height), the die thickness was slightly enlarged to provide the correct height. The C5 solder layer is modeled as a cuboid with dimensions 33x33x0.4 mm and orthotropic thermal conductivity of 0.034 W/(m • K) in the xy-plane and 9.6 W/(m • K) in the z-direction. An LGA solder layer would be modeled as a collapsed thermal resistance with thermal conductivity of 9.6W/(m • K) and an effective height of 0.1 mm. The thermal model uses approximate dimensions to reduce grid. Please refer to the case outline for actual dimensions.

Another useful equation is:

$$V_H - V_L = n\frac{KT}{q}\left[ln\frac{I_H}{I_L}\right]$$

Where:

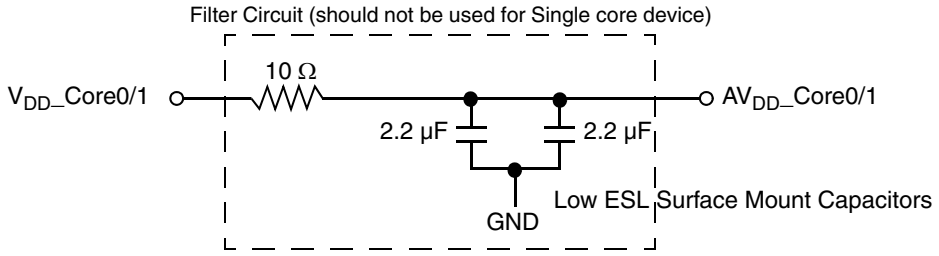
I_{fw} = Forward current
I_s = Saturation current
V_d = Voltage at diode
V_f = Voltage forward biased
V_H = Diode voltage while I_H is flowing
V_L = Diode voltage while I_L is flowing
I_H = Larger diode bias current
I_L = Smaller diode bias current
q = Charge of electron (1.6×10^{-19} C)
n = Ideality factor (normally 1.0)
K = Boltzman's constant (1.38×10^{-23} Joules/K)
T = Temperature (Kelvins)

The ratio of I_H to I_L is usually selected to be 10:1. The above simplifies to the following:

$$V_H - V_L = 1.986 \times 10^{-4} \times nT$$

Solving for T, the equation becomes:

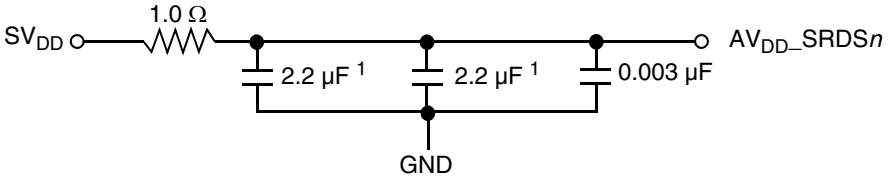
$$nT = \frac{V_H - V_L}{1.986 \times 10^{-4}}$$



Note: For single core device the filter circuit (in the dashed box) should be removed and AV_{DD}_Core1 should be tied to ground with a weak (2-10 kΩ) pull-down resistor.

Figure 64. MPC8641 PLL Power Supply Filter Circuit (for cores)

The AV_{DD}_SRDS*n* signals provide power for the analog portions of the SerDes PLL. To ensure stability of the internal clock, the power supplied to the PLL is filtered using a circuit similar to the one shown in following figure. For maximum effectiveness, the filter circuit is placed as closely as possible to the AV_{DD}_SRDS*n* balls to ensure it filters out as much noise as possible. The ground connection should be near the AV_{DD}_SRDS*n* balls. The 0.003-µF capacitor is closest to the balls, followed by the two 2.2-µF capacitors, and finally the 1 Ω resistor to the board supply plane. The capacitors are connected from AV_{DD}_SRDS*n* to the ground plane. Use ceramic chip capacitors with the highest possible self-resonant frequency. All traces should be kept short, wide and direct.



1. An 0805 sized capacitor is recommended for system initial bring-up.

Figure 65. SerDes PLL Power Supply Filter

Note the following:

- AV_{DD}_SRDS*n* should be a filtered version of SV_{DD}.
- Signals on the SerDes interface are fed from the SV_{DD} power plan.

20.2.2 PLL Power Supply Sequencing

For details on power sequencing for the AV_{DD} type and supplies refer to Section 2.2, "Power Up/Down Sequence."

20.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8641 system, and the device itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system

designer place at least one decoupling capacitor at each OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT pin of the device. These decoupling capacitors should receive their power from separate OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT and GND power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT planes, to enable quick recharging of the smaller chip capacitors. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON).

20.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}_SRDS*n*) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

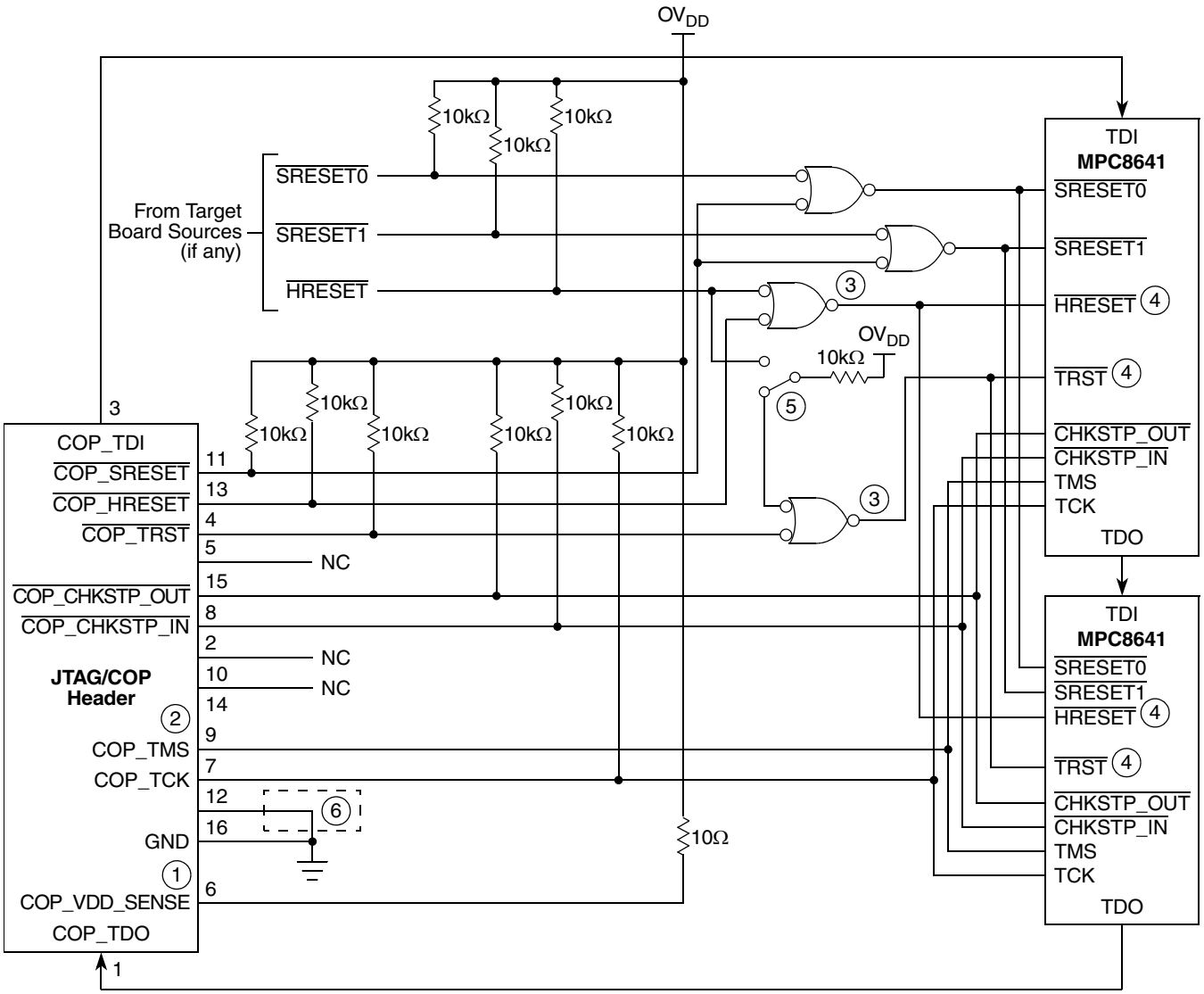
- First, the board should have at least 10 x 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the device. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the device as close to the supply and ground connections as possible.
- Second, there should be a 1-µF ceramic chip capacitor on each side of the device. This should be done for all SerDes supplies.
- Third, between the device and any SerDes voltage regulator there should be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

20.5 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. In general all unused active low inputs should be tied to OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT, XV_{DD}_SRDS*n*, and SV_{DD} as required and unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Special cases:

DDR - If one of the DDR ports is not being used the power supply pins for that port can be connected to ground so that there is no need to connect the individual unused inputs of that port to ground. Note that these power supplies can only be powered up again at reset for functionality to occur on the DDR port. Power supplies for other functional buses should remain powered.



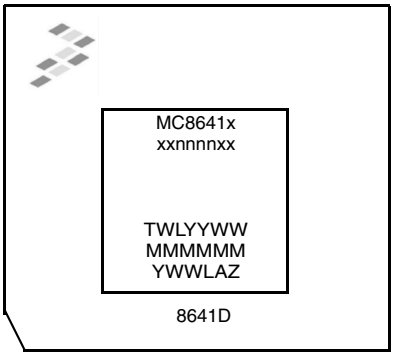
Notes:

1. Populate this with a 10Ω resistor for short circuit/current-limiting protection.
2. KEY location; pin 14 is not physically present on the COP header.
3. Use a AND gate with sufficient drive strength to drive two inputs.
4. The COP port and target board should be able to independently assert $\overline{\text{HRESET}}$ and $\overline{\text{TRST}}$ to the processor in order to fully control the processor as shown above.
5. This switch is included as a precaution for BSDL testing. The switch should be open during BSDL testing to avoid accidentally asserting the $\overline{\text{TRST}}$ line. If BSDL testing is not being performed, this switch should be closed or removed.
6. Although pin 12 is defined as a No-Connect, some debug tools may use pin 12 as an additional GND pin for improved signal integrity.

Figure 69. JTAG/COP Interface Connection for Multiple MPC8641 Devices in Daisy Chain Configuration

21.2 Part Marking

Parts are marked as the example shown in Figure 70.



NOTE:
TWLYYWW is the test code
MMMMMM is the M00 (mask) number.
YWWLAZ is the assembly traceability code.

Figure 70. Part Marking for FC-CBGA Device

22 Document Revision History

Table 76 provides a revision history for the MPC8641D hardware specification.

Table 76. Document Revision History

Revision	Date	Substantive Change(s)
3	05/2014	• Updated the Serial RapidIO equation in Section 4.4, “Platform Frequency Requirements for PCI-Express and Serial RapidIO” • Updated Section 19.2.4, “Temperature Diode,” by removing the ideality factor value. • Added VJ package type designator and footnotes to Table 74, “Part Numbering Nomenclature” and Section 16.1, “Package Parameters for the MPC8641.”
2	07/2009	• Added note 8 to Table 49, “Differential Transmitter (TX) Output Specifications.” • Added Revision E to Table 74, “Part Numbering Nomenclature.”
1	11/2008	• Added Section 4.4, “Platform Frequency Requirements for PCI-Express and Serial RapidIO.” • Removed the statement “Note that core processor speed of 1500 MHz is only available for the MPC8641D (dual core)” from Note 2 in Table 74 because a 1500 MHz core is offered for both MPC8641D (dual core) and MPC8641 (single core). • Added Note 8 to Figure 57 and Figure 58.
0	07/2008	• Initial Release